

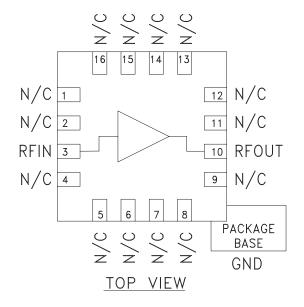


Typical Applications

This amplifier is ideal for high linearity applications:

- Multi-Carrier Systems
- GSM, GPRS & EDGE
- CDMA & WCDMA
- PHS

Functional Diagram



HMC455LP3 / 455LP3E

InGaP HBT ½ Watt High IP3 AMPLIFIER, 1.7 - 2.5 GHz

Features

Output IP3: +42 dBm Gain: 13 dB 56% PAE @ +28 dBm Pout +19 dBm W-CDMA Channel Power @ -45 dBc ACP 3x3 mm QFN SMT Package

General Description

The HMC455LP3 & HMC455LP3E are high output IP3 GaAs InGaP Heterojunction Bipolar Transistor (HBT) ½ watt MMIC amplifiers operating between 1.7 and 2.5 GHz. Utilizing a minimum number of external components the amplifier provides 13 dB of gain and +28 dBm of saturated power at 56% PAE from a single +5 Vdc supply voltage. The high output IP3 of +42 dBm coupled with the low VSWR of 1.4:1 make the HMC455LP3 & HMC455LP3E ideal driver amplifiers for PCS/3G wireless infrastructures. A low cost, leadless 3x3 mm QFN surface mount package (LP3) houses the linear amplifier. The LP3 provides an exposed base for excellent RF and thermal performance.

Electrical Specifications, $T_{a} = +25^{\circ} C$, Vs = +5V

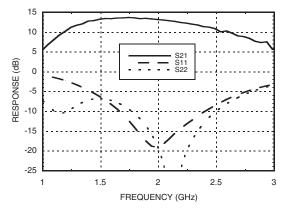
| Parameter | Min. | Тур. | Max. | Min. | Тур. | Max. | Min. | Тур. | Max. | Units |
|-----------------------------------------|-----------|-------|-----------|------|-----------|------|------|-------|------|---------|
| Frequency Range | 1.7 - 1.9 | | 1.9 - 2.2 | | 2.2 - 2.5 | | GHz | | | |
| Gain | 11.5 | 13.5 | | 10.5 | 13 | | 9 | 11.5 | | dB |
| Gain Variation Over Temperature | | 0.012 | 0.02 | | 0.012 | 0.02 | | 0.012 | 0.02 | dB / °C |
| Input Return Loss | | 13 | | | 15 | | | 10 | | dB |
| Output Return Loss | | 10 | | | 18 | | | 15 | | dB |
| Output Power for 1dB Compression (P1dB) | 24 | 27 | | 24.5 | 27.5 | | 23 | 26 | | dBm |
| Saturated Output Power (Psat) | | 28.5 | | | 28 | | | 27 | | dBm |
| Output Third Order Intercept (IP3) | 37 | 40 | | 39 | 42 | | 37 | 40 | | dBm |
| Noise Figure | | 7 | | | 6 | | | 6 | | dB |
| Supply Current (Icq) | | 150 | | | 150 | | | 150 | | mA |

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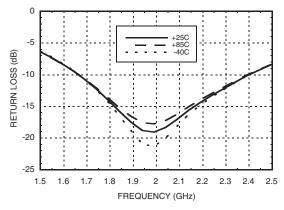




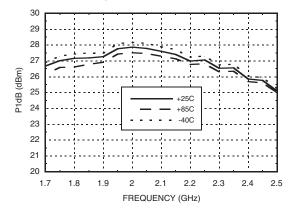
Broadband Gain & Return Loss



Input Return Loss vs. Temperature



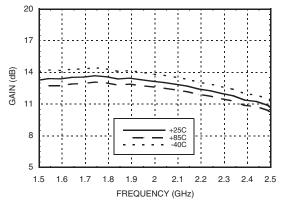
P1dB vs. Temperature



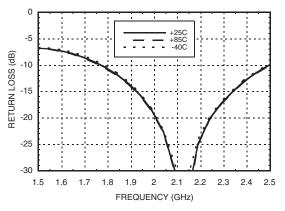
HMC455LP3 / 455LP3E

InGaP HBT ½ Watt High IP3 AMPLIFIER, 1.7 - 2.5 GHz

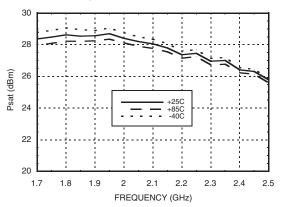
Gain vs. Temperature



Output Return Loss vs. Temperature



Psat vs. Temperature



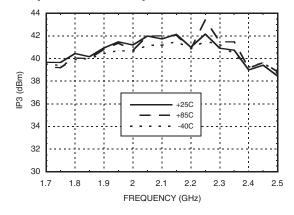
Data shown is tuned for 1.85 - 2.2 GHz, contact HMC Applications for recommended 1.7 - 1.85 GHz & 2.2 - 2.5 GHz tuning circuits.

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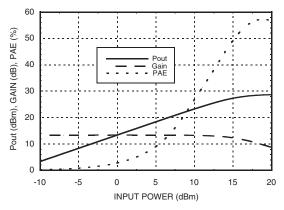




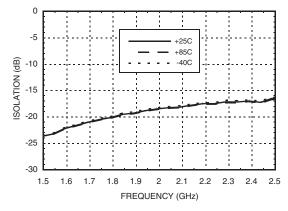
Output IP3 vs. Temperature



Power Compression @ 1.95 GHz

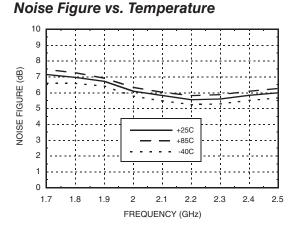


Reverse Isolation vs. Temperature

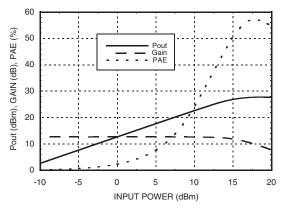


HMC455LP3 / 455LP3E

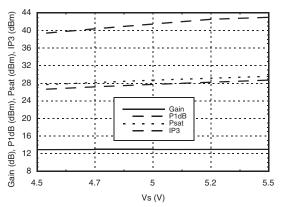
InGaP HBT ½ Watt High IP3 AMPLIFIER, 1.7 - 2.5 GHz



Power Compression @ 2.15 GHz



Gain, Power & IP3 vs. Supply Voltage @ 1.95 GHz



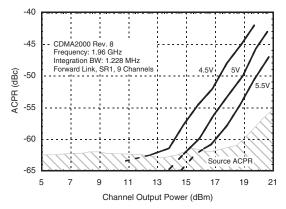
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ACPR vs. Supply Voltage @ 1.96 GHz CDMA 2000, 9 Channels Forward



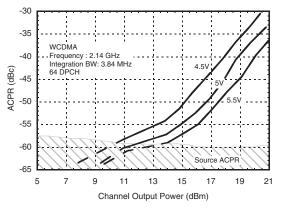
Absolute Maximum Ratings

| Collector Bias Voltage (Vcc) | +6.0 Vdc |
|---------------------------------------------------------------|----------------|
| RF Input Power (RFIN)(Vs = +5Vdc) | +25 dBm |
| Junction Temperature | 150 °C |
| Continuous Pdiss (T = 85 °C) (derate 16 mW/°C above 85 °C) | 1.04 W |
| Thermal Resistance (junction to ground paddle) | 63 °C/W |
| Storage Temperature | -65 to +150 °C |
| Operating Temperature | -40 to +85 °C |

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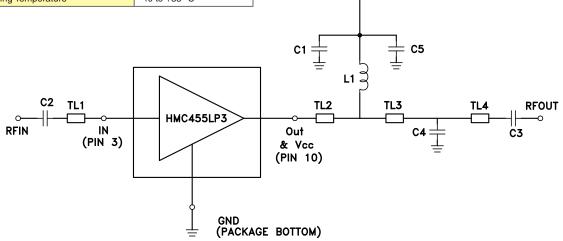
ACPR vs. Supply Voltage @ 2.14 GHz W-CDMA, 64 DPCH





Application Circuit

Vs (5V)



| | TL1 | TL2 | TL3 | TL4 | |
|---------------------------------------------|--------|--------|--------|--------|--|
| Impedance | 50 Ohm | 50 Ohm | 50 Ohm | 50 Ohm | |
| Physical Length | 0.33" | 0.18" | 0.13" | 0.04" | |
| Electrical Length | 34° | 19° | 13.5° | 4° | |
| PCB Material: 10 mil Rogers 4350, Er = 3.48 | | | | | |

| Recommended Component Values | | | | |
|------------------------------|--------|--|--|--|
| L1 | 8.2 nH | | | |
| C1 | 2.2 μF | | | |
| C2, C3 | 3.0 pF | | | |
| C4 | 0.9 pF | | | |
| C5 | 100 pF | | | |

Data shown is tuned for 1.85 - 2.2 GHz, contact HMC

Applications for recommended 1.7 - 1.85 GHz & 2.2 - 2.5 GHz tuning circuits.

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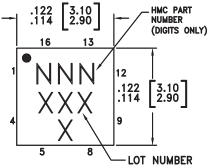


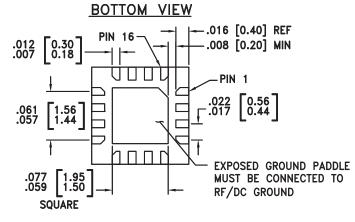
HMC455LP3 / 455LP3E

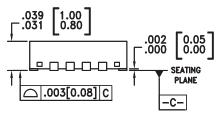
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Outline Drawing







NOTES:

v02.0605

1. LEADFRAME MATERIAL: COPPER ALLOY

- 2. DIMENSIONS ARE IN INCHES [MILLIMETERS]
- 3. LEAD SPACING TOLERANCE IS NON-CUMULATIVE
- PAD BURR LENGTH SHALL BE 0.15mm MAXIMUM.
 - PAD BURR HEIGHT SHALL BE 0.05mm MAXIMUM.
- 5. PACKAGE WARP SHALL NOT EXCEED 0.05mm.
- 6. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.
- 7. REFER TO HITTITE APPLICATION NOTE FOR SUGGESTED LAND PATTERN.

Package Information

| Part Number | Package Body Material | Lead Finish | MSL Rating | Package Marking ^[3] | |
|-------------|----------------------------------------------------|---------------|---------------------|--------------------------------|--|
| HMC455LP3 | Low Stress Injection Molded Plastic | Sn/Pb Solder | MSL1 ^[1] | 455 XXXX | |
| HMC455LP3E | RoHS-compliant Low Stress Injection Molded Plastic | 100% matte Sn | MSL1 ^[2] | <u>455</u> XXXX | |

[1] Max peak reflow temperature of 235 $^\circ\text{C}$

[2] Max peak reflow temperature of 260 °C

[3] 4-Digit lot number XXXX

Pin Descriptions

| Pin Number | Function | Description | Interface Schematic |
|-------------------------|----------|-------------------------------------------------------------------------------|---------------------|
| 1, 2, 4 - 9, 11 - 16 | N/C | This pin may be connected to RF ground. | |
| 3 | RFIN | This pin is AC coupled. An off chip series matching capacitor is required. | |
| 10 | RFOUT | RF output and DC Bias for the output stage. | |
| | GND | Package bottom must be connected to RF/DC ground. | |

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